

Q3
sub 4
19. (Amended) A method according to claim 18 wherein said channel region is substantially intrinsic type or p-type.

24. (Amended) A method according to claim 23 wherein said channel region is substantially intrinsic type or p-type.

25
sub 6
30. (Amended) A method according to claim 23 wherein said channel region is substantially intrinsic type or p-type.

D6
sub 8
53. (Amended) A method for fabricating a semiconductor device, said semiconductor device having at least one thin film transistor comprising a semiconductor film formed adjacent to a gate electrode with a gate insulating film therebetween, said method comprising the steps of:
forming said semiconductor film over a substrate;
forming an insulating film on said semiconductor film;
introducing boron into at least a portion of said semiconductor film through said insulating film, said portion becoming at least a channel region of said thin film transistor; and
removing said insulating film.

Please add new claims 62-64 as follows:

D7
--62. A method according to claim 18 wherein said crystallizing said semiconductor film by laser irradiation is performed through said insulating film.

63. A method according to claim 23 wherein said crystallizing said semiconductor film by laser irradiation is performed through said insulating film.

64. A method according to claim 29 wherein said crystallizing said semiconductor film by laser irradiation is performed through said insulating film.--
